



Science and  
Technology  
Facilities Council



# RF Surface Resistance Measurements on Planar Samples at STFC

*9<sup>th</sup> IFAST WP9 Meeting  
18<sup>th</sup> April 2023*

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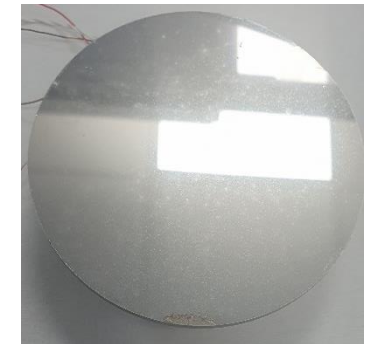
# Facility Reminder

# The Choke Cavity Facility

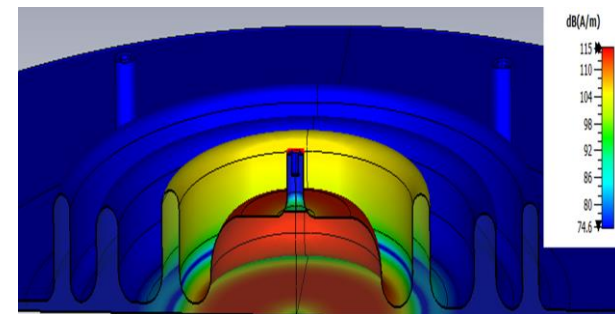
- **Two part test cavity in LHe-free cryostat:**
  - Bulk Nb choke cavity
  - Planar disk - **90 - 130 mm** diameter, **1 – 10 mm** thickness
- **RF-DC compensation**  $\rightarrow R_s(T, B)$
- **VNA measurements**  $\rightarrow \Delta f \rightarrow \Delta\lambda$
- **Parameters:**
  - $f_0 = 7.8$  GHz
  - $T_{\text{sample}} \geq 4$  K
  - RF Power up to 1 W (for now!)
  - $B_{\text{sample, pk}} \leq 1$  mT



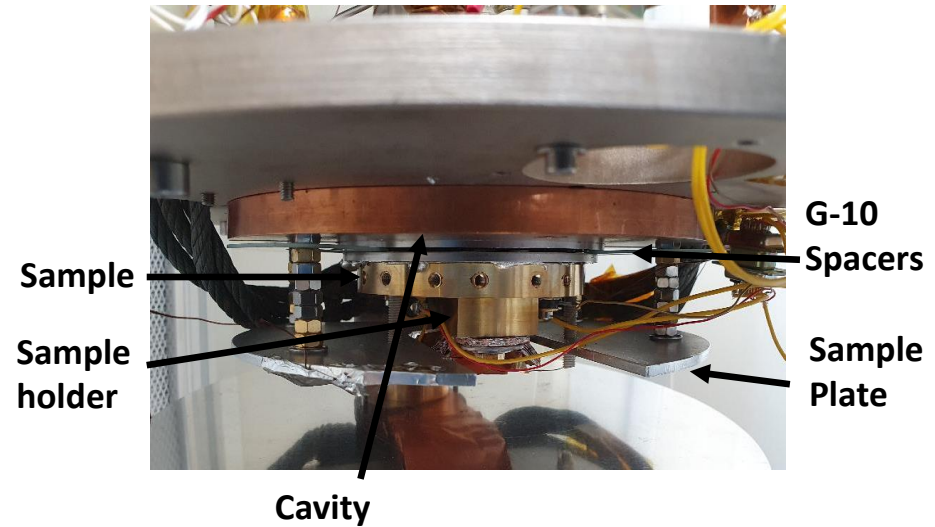
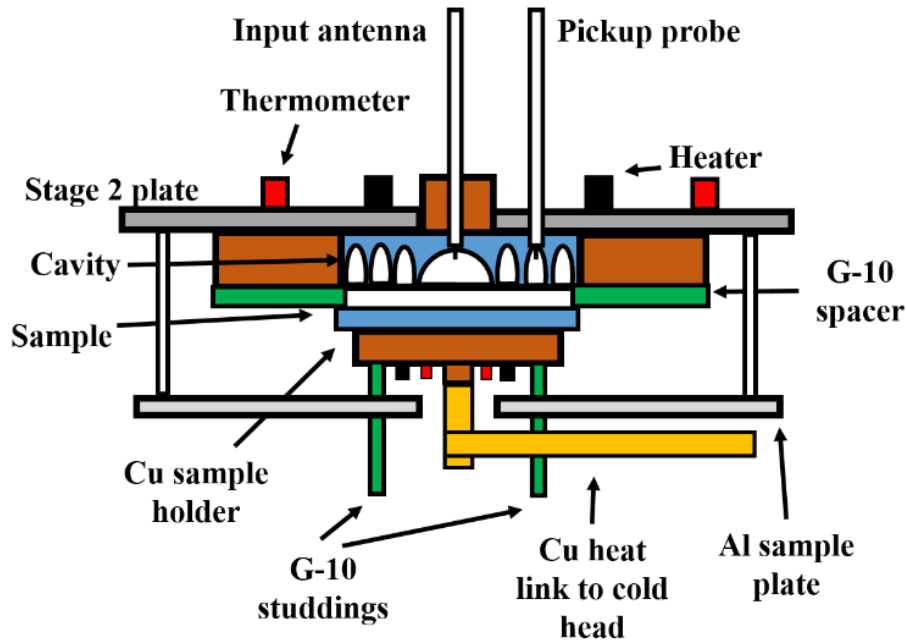
Choke cavity



Planar disk

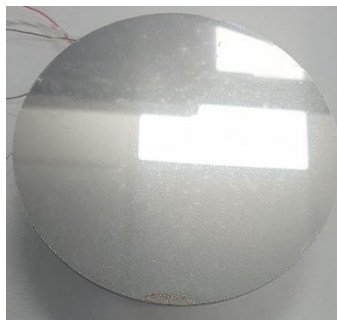
**B-fields**

# The Choke Cavity Facility



1 sample test ( $R_s(T)$ )/2 days

# Cu Samples



**Diamond Turned (DT) from RAL**  
( $S_a \sim 2-3$  nm,  $S_q \sim 5-6$  nm)



**Metallographic Polishing (MP) from IJCLab**  
*courtesy of D. Longuevergne & O. Hryhorenko*  
( $S_a \sim 20$  nm, Ave  $S_z \sim 2.5$   $\mu$ m)



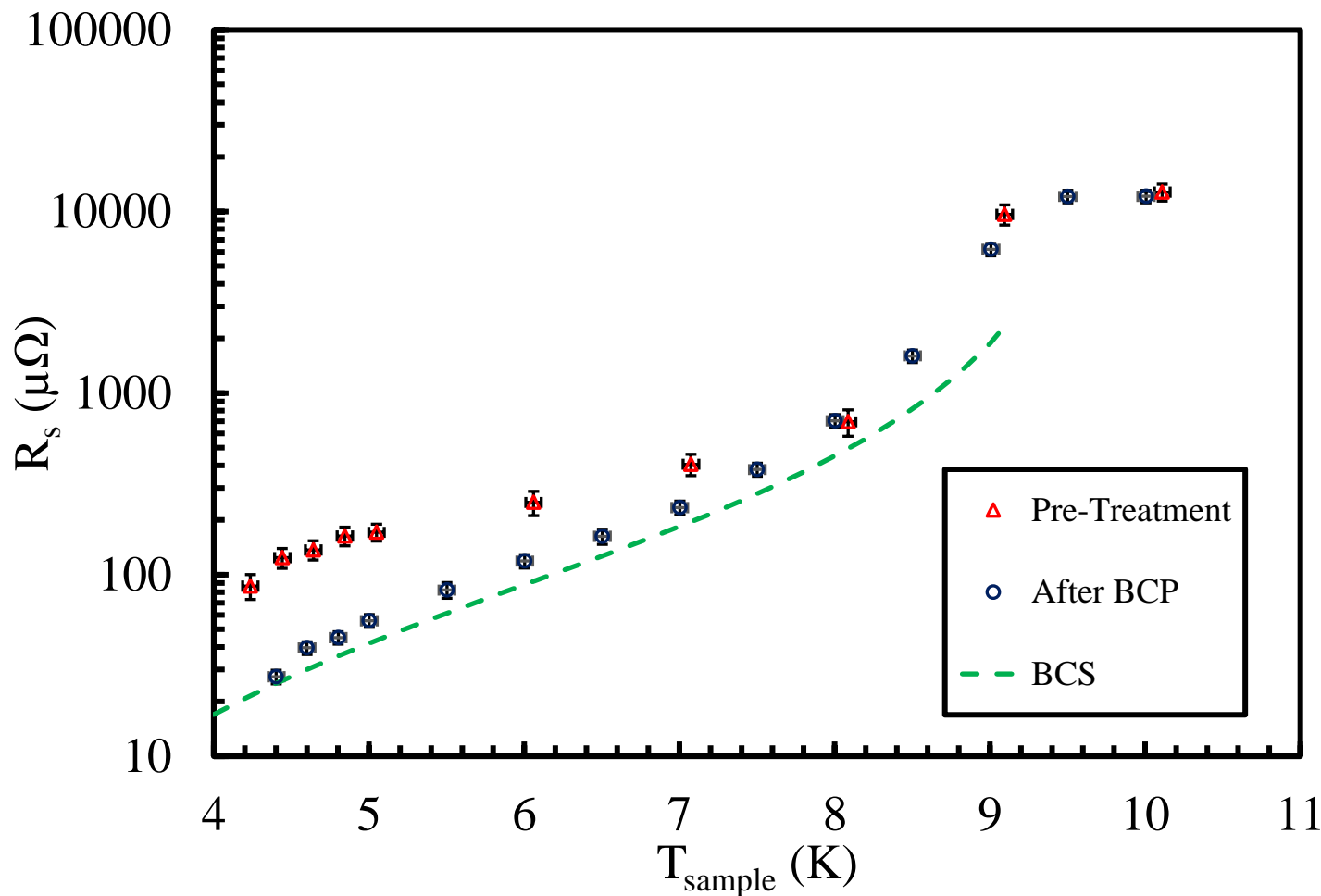
**EP, SUBU, EP + SUBU from INFN**  
*courtesy of E. Chyhyrynets and C. Pira*



**Samples are indium  
brazed to sample  
holder under vacuum  
at  $\sim 160$   $^{\circ}$ C**

# RF Measurements of a Bulk Nb Sample

# Bulk Nb



**Bulk Nb:**  $RRR = 300$ , BCP  
with 60-100  $\mu\text{m}$   
removed  
*courtesy of E.  
Chyhyrnyts*

**\* 4 more bulk Nb**  
( $RRR = 300$ ) available  
for treatment

# RF Measurements of Nb on Cu Samples

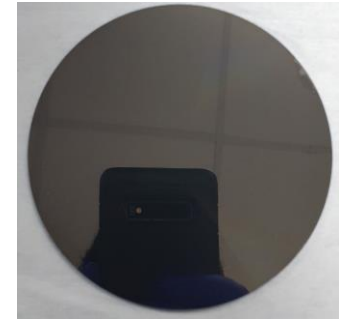
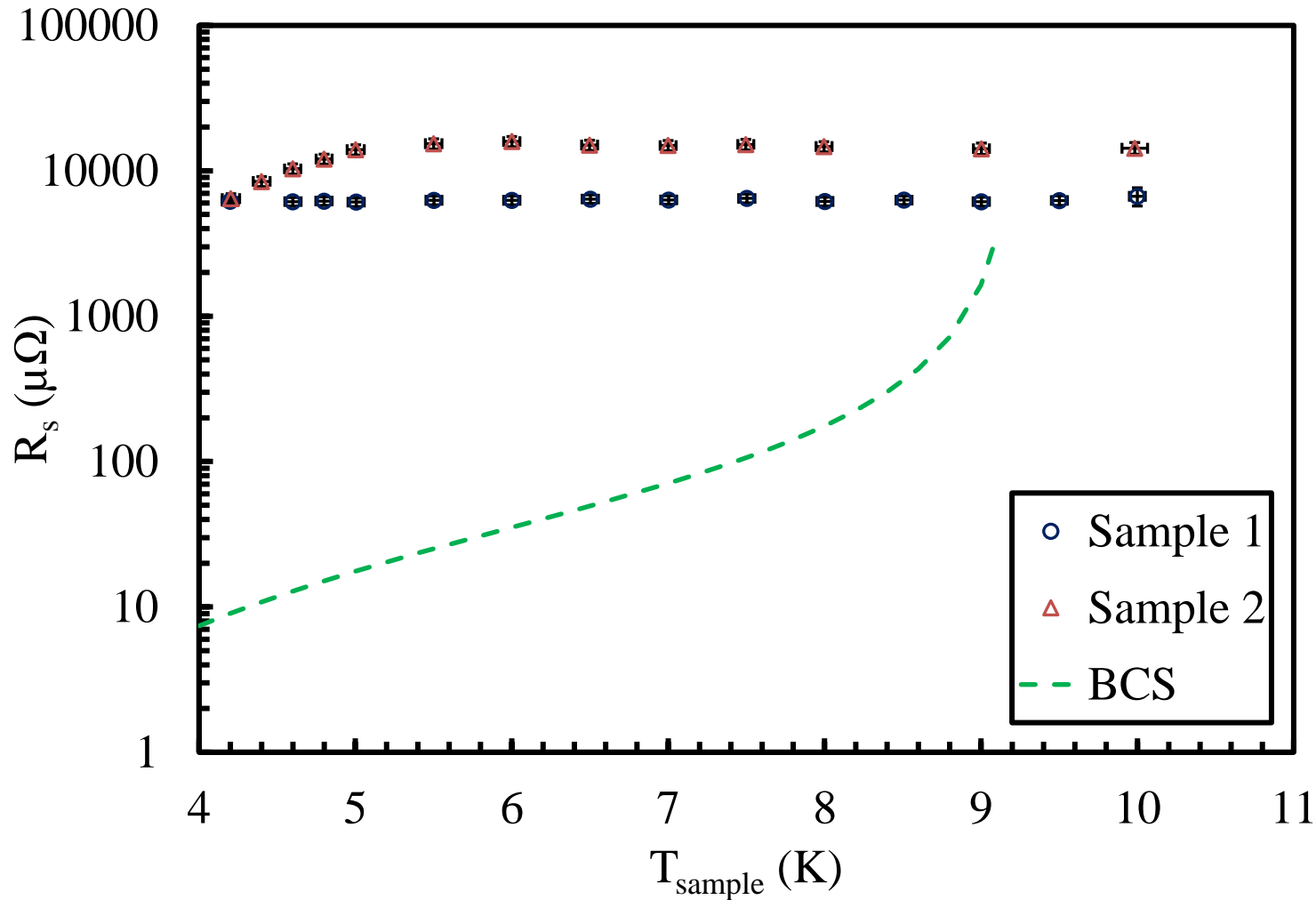


# Nb on Cu Samples Tested

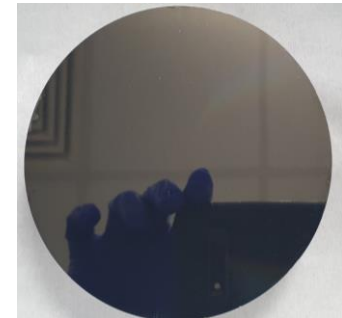
Sample	Substrate Preparation	Deposition Temperature (°C)	~ Thickness (μm)
<b>Effect of film thickness with DC magnetron</b>			
1	DT	300 - 350	0.6
2	DT	300 - 350	1.2
<b>Effect of deposition temperature with HiPIMS</b>			
3	DT	400 - 450	3
4	DT	RT	3
5	DT	300 - 350	3

**\* Surface analysis to be shown at 10<sup>th</sup> meeting**

# Samples 1 & 2

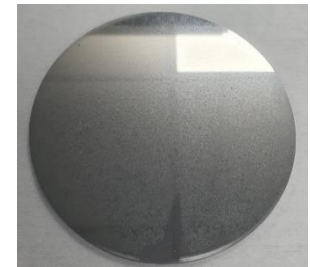
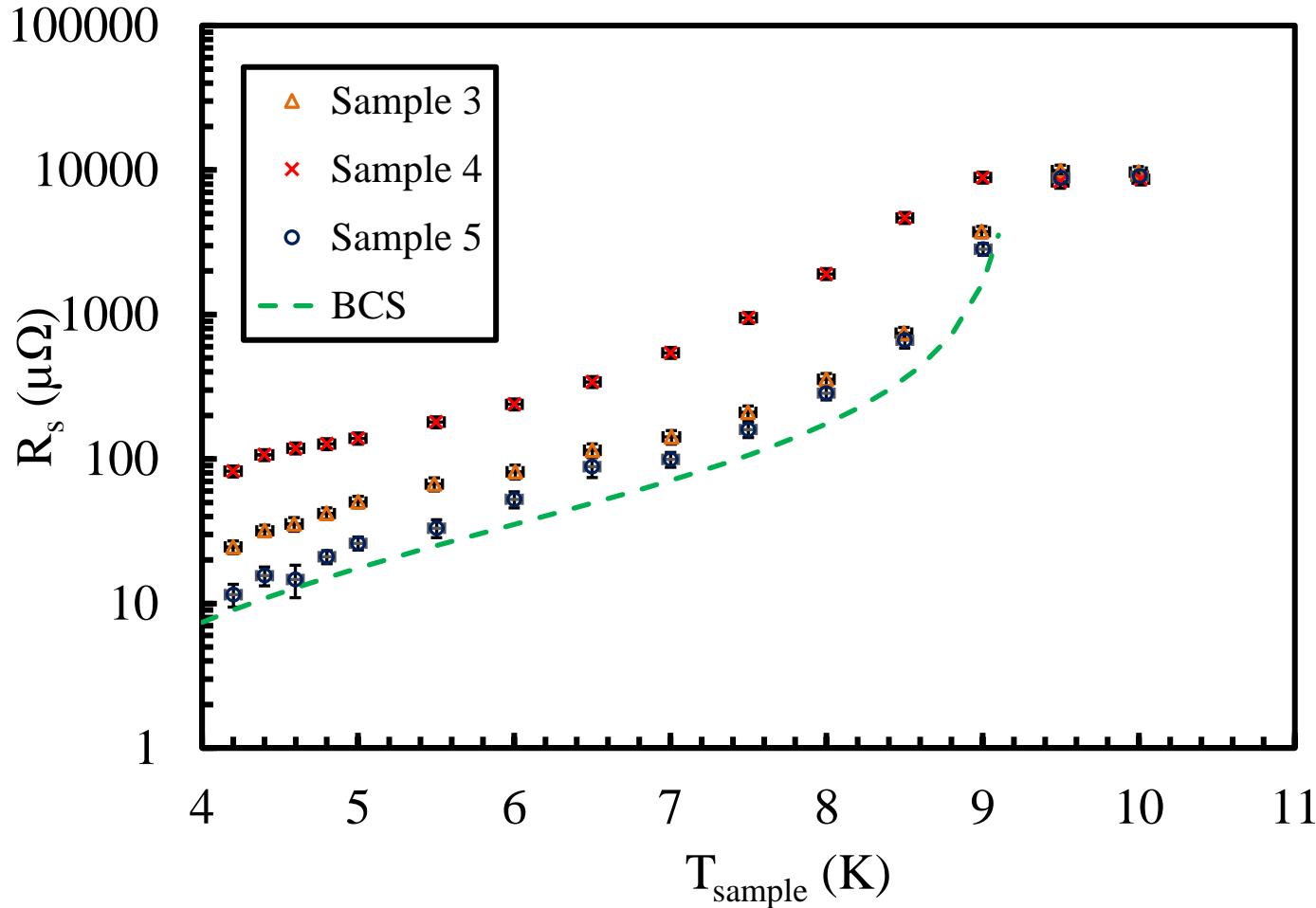


**Sample 1:** DC magnetron, 300 – 350 °C, ~ 0.6  $\mu\text{m}$

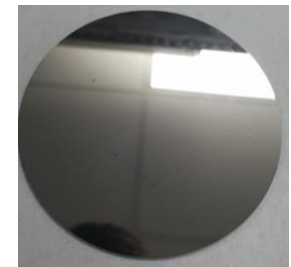


**Sample 2:** DC magnetron, 300 – 350 °C, ~ 1.2  $\mu\text{m}$

# Samples 3 - 5



**Sample 3:** 400 – 450 °C, ~ 3  $\mu\text{m}$

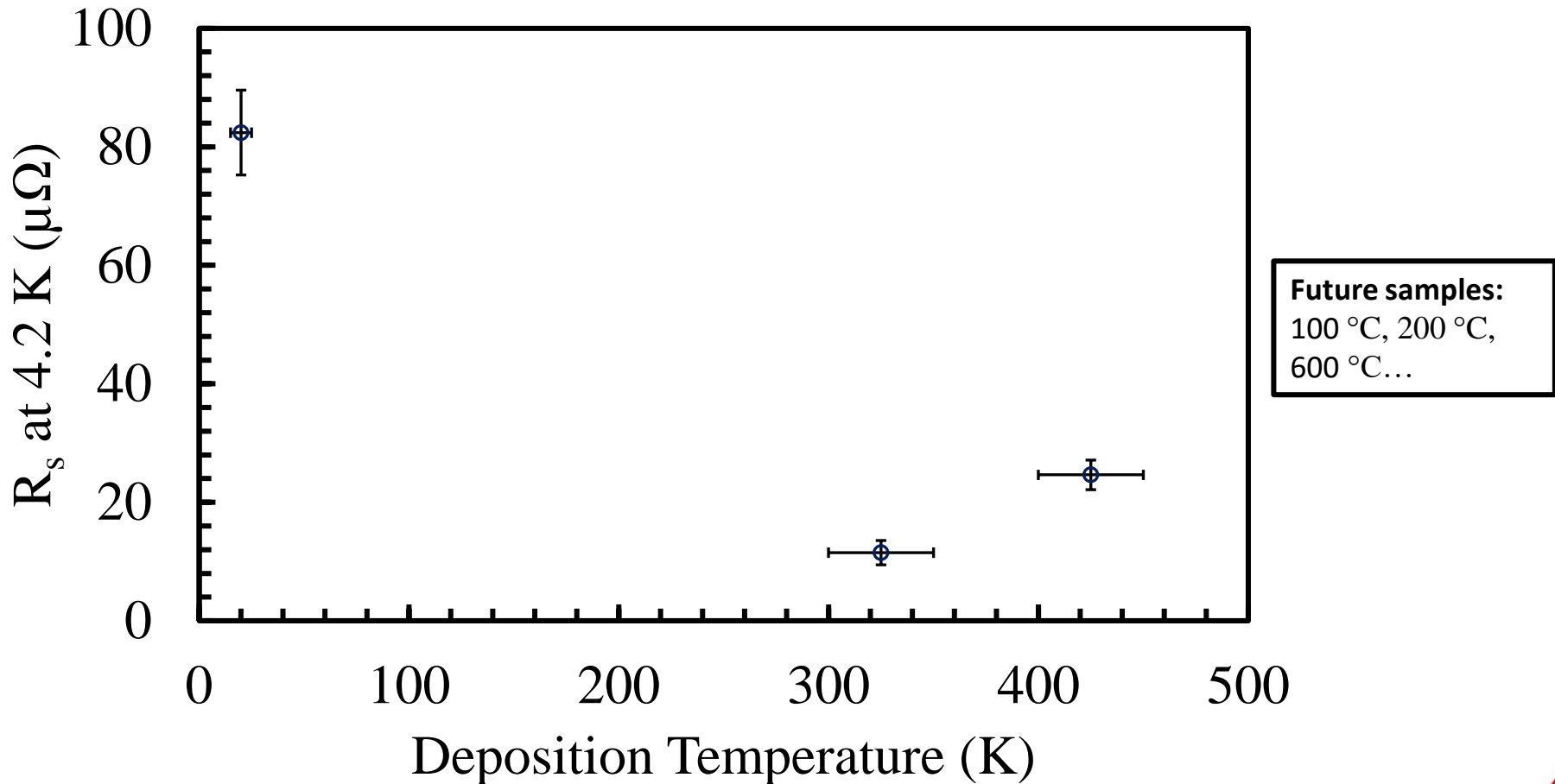


**Sample 4:** RT, ~ 3  $\mu\text{m}$



**Sample 5:** 300 – 350 °C, ~ 3  $\mu\text{m}$

# Samples 3 – 5: towards optimising deposition temperature

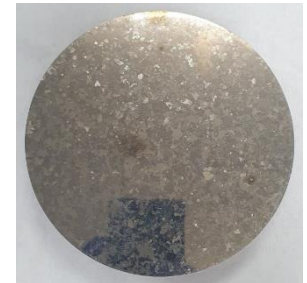
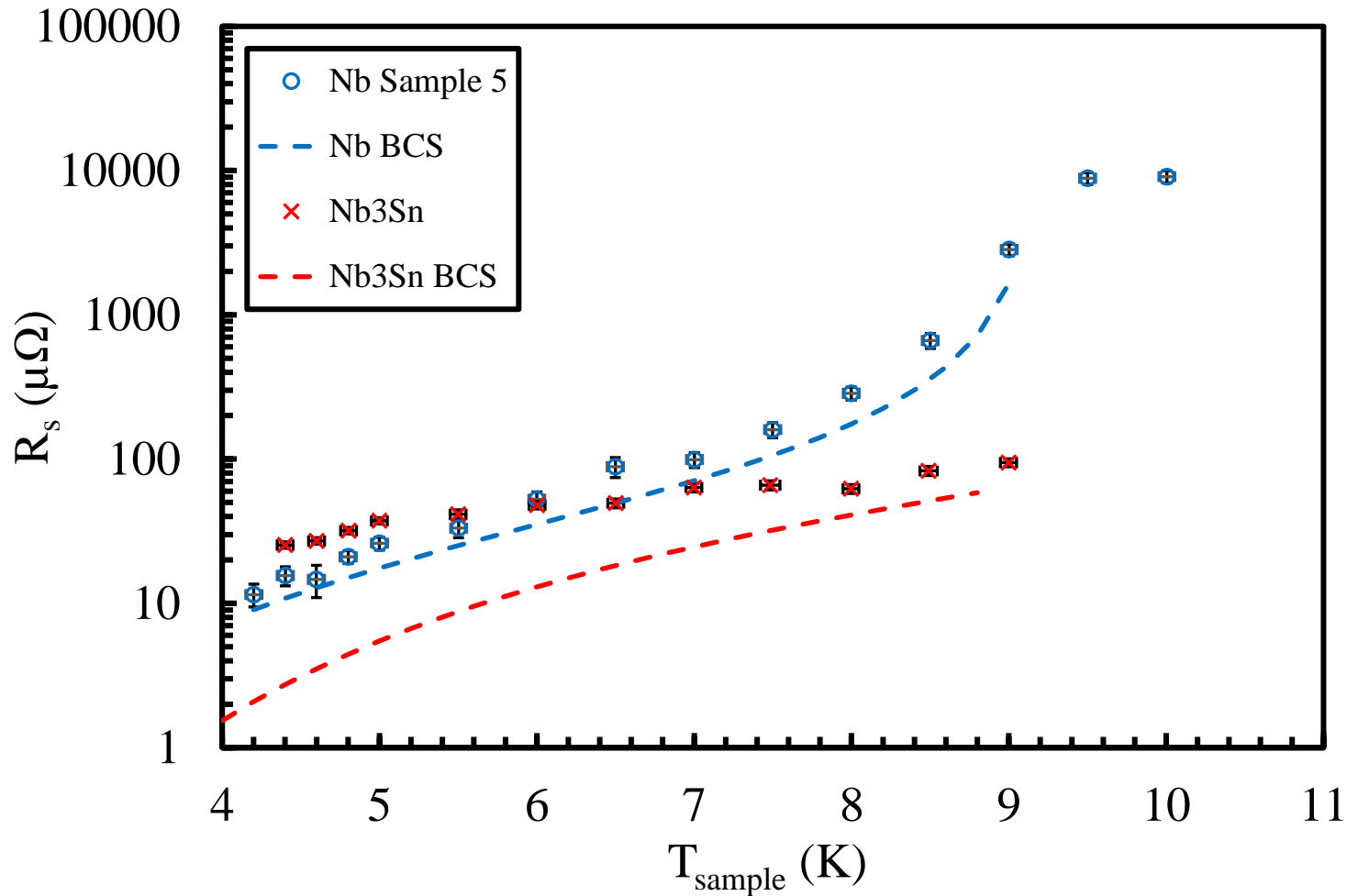


# Future Nb Samples

Sample	Substrate Preparation	Deposition Temperature (°C)	Thickness (μm)
<b>Effect of deposition temperature with HiPIMS</b>			
3	DT	400 - 450	~ 3
4	DT	RT	~ 3
5	DT	300 - 350	~ 3
6	DT	600-650	~ 3
7	DT	100	~ 3
8	DT	200	~ 3
<b>Effect of HiPIMS + positive kick</b>			
...	DT	?	~ 3
<b>Effect of substrate preparation</b>			
...	MP, EP, SUBU, EP + SUBU	?	~ 3

# RF Measurements of a $\text{Nb}_3\text{Sn}$ Sample

# Nb<sub>3</sub>Sn Sample



**Nb<sub>3</sub>Sn Sample:** DC magnetron, ~ 600°C, ~ 600 nm

# Next Steps

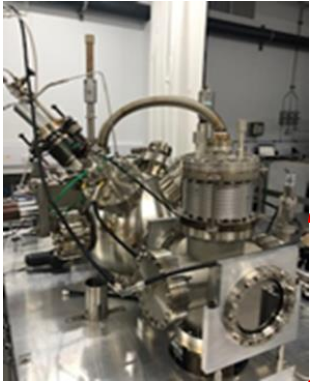


# From planar samples to real cavities

**Aim:** Best performing flat samples → split cavities

## 3 sets of samples:

1. Nb coated planar samples
  - Low power RF test with choke cavity
  - High power RF test with QPR
2. Split cavity deposited with planar magnetron & planar target
  - RF test
3. Split cavity deposited with cylindrical magnetron & tubular target
  - RF test



# Current Status & Future Plans

1. Optimise parameters of Nb thin films → Baseline for multilayers
2. Continue Nb<sub>3</sub>Sn, NbTiN, (& V<sub>3</sub>Si) single layer studies
3. Multilayers (on TF Nb and/or bulk Nb)

- Cut samples → MFP (Liam) & surface analysis (Reza/Chris) etc
- Test IJCLab treated bulk Nb 2 choke cavity
- Move to an RF bunker → higher peak fields (overlapping with QPR)
- Happy to accept samples on disks 90-130 mm diameter (up to 10 mm thickness)
  - Can provide unpolished or polished (mainly DT) Cu
  - Contact: [daniel.seal@cockcroft.ac.uk](mailto:daniel.seal@cockcroft.ac.uk)
- Potential for laser treatment at RTU and/or flash at HZDR?

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**CEA:** C. Antoine



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# Thank you for listening

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